

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,011,978 B2
APPLICATION NO. : 09/932003
DATED : March 14, 2006
INVENTOR(S) : Cem Basceri

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page, Col. 2, FOREIGN PATENT DOCUMENTS –

Replace “EP 0 388 947 A1 9/1990”

With --EP 0 388 957 A1 9/1990--

Page 2, Col. 2, OTHER PUBLICATIONS –

Add: --DISSERTATION: Basceri, Cem, “Electrical and Dielectric Properties of (Ba, Sr)TiO₃ Thin Film Capacitors for Ultra High Density Dynamic Random Access Memories”, 1997, 171 pgs.--

Col. 1, line 32 –

Replace “a very thin dielectric films for the 3-dimensional capacitors”

With --very thin dielectric films for the 3-dimensional capacitors--

Col. 6, line 38 –

Replace “embodiment, the formation of dielectric materials 12, 124”

With --embodiment, the formation of dielectric materials 122, 124--

Signed and Sealed this

Fourth Day of March, 2008

A handwritten signature in black ink, appearing to read "Jon W. Dudas". The signature is stylized with a large, looped initial "J" and a distinct "D".

JON W. DUDAS
Director of the United States Patent and Trademark Office